Amendments to the Claims

Claims 1-90 (cancelled).

Claim 91 (previously presented): A method of forming a plurality of floating gate transistors comprising:

forming an oxide-comprising layer against and physically contacting a semiconductive substrate;

forming a first layer against and physically contacting the oxide-comprising layer, wherein the first layer comprises semiconductive material and a dopant, at least some of the dopant physically contacting the oxide-comprising layer;

after forming the first layer, forming a second layer against and physically contacting the first layer, wherein the second layer comprises semiconductive material, the semiconductive material of the second layer being substantially undoped;

forming a third layer over the second layer, the third layer comprising dielectric material;

forming a fourth layer over the third layer, the fourth layer comprising conductive material;

etching the oxide-comprising layer and the first through fourth layers to form a plurality of floating gates;

forming source and drain regions laterally proximate the floating gates;

forming an oxide layer over the regions and the floating gates; and

disposing a plug of conductive contact film operatively adjacent at least one of the drain regions, the plug of conductive material being electrically connected to the at least one of the drain regions.

Claim 92 (previously presented): The method of claim 91 wherein before forming the third layer over the second layer, the first and second layers are etched to define floating gate wings over the oxide-comprising layer.

Claim 93 (previously presented): The method of claim 91 wherein the first and second layers comprise a material having a thickness, and the forming of the first and second layers comprises forming the first layer to occupy at least 25 percent of the material thickness.

Claim 94 (previously presented): The method of claim 91 wherein the first and second layers comprise a material having a thickness, and the forming of the first and second layers comprises forming the first layer to occupy less than 75 percent of the material thickness.

Claim 95 (previously presented): The method of claim 91 wherein the forming of the first layer comprises forming the first layer to have a dopant concentration of greater than or equal to about $1 \times 10^{18} \text{cm}^{-3}$.

Claim 96 (previously presented): The method of claim 91 wherein the forming of the first layer comprises:

forming a polysilicon-comprising layer upon the oxide-comprising layer; and

doping the polysilicon-comprising layer with phosphorous dopant material to a concentration of greater than or equal to about $1 \times 10^{18} \text{cm}^{-3}$.

Claim 97 (previously presented): The method of claim 96 wherein the doping the polysilicon-comprising layer is to a degree sufficient to define a sheet resistance of between 300 ohm/sq. and 400 ohm/sq.

Claim 98 (previously presented): The method of claim 91 wherein:

the first and second layers comprise a material having a thickness, and the forming of the first and second layers comprises forming the first layer to occupy less than 75 percent of the material thickness; and

the forming of the first layer comprises forming the first layer to have a dopant concentration of greater than or equal to about $1 \times 10^{18} cm^{-3}$.

Claim 99 (previously presented): The method of claim 91 wherein the third layer comprises nitride.

Claim 100 (previously presented): The method of claim 91 wherein the first and second layers each have a thickness and the first and second layer thicknesses are substantially equal.

Claim 101 (previously presented): The method of claim 91 wherein the first and second layers each have a thickness and the first and second layer thicknesses are substantially different.

Claim 102 (previously presented): The method of claim 91 wherein a thickness of the first layer is less than about 550 Angstroms.

Claim 103 (previously presented): The method of claim 91 wherein a thickness of the first layer is between 450 Angstroms and 550 Angstroms.